

# Emanuele Ucelli

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2986703/publications.pdf>

Version: 2024-02-01

19  
papers

1,220  
citations

566801

15  
h-index

839053

18  
g-index

19  
all docs

19  
docs citations

19  
times ranked

1666  
citing authors

#	ARTICLE	IF	CITATIONS
1	Direct correlation of crystal structure and optical properties in wurtzite/zinc-blende GaAs nanowire heterostructures. <i>Physical Review B</i> , 2011, 83, .	1.1	193
2	Untangling the Electronic Band Structure of Wurtzite GaAs Nanowires by Resonant Raman Spectroscopy. <i>ACS Nano</i> , 2011, 5, 7585-7592.	7.3	126
3	Three-Dimensional Multiple-Order Twinning of Self-Catalyzed GaAs Nanowires on Si Substrates. <i>Nano Letters</i> , 2011, 11, 3827-3832.	4.5	123
4	P-Doping Mechanisms in Catalyst-Free Gallium Arsenide Nanowires. <i>Nano Letters</i> , 2010, 10, 1734-1740.	4.5	110
5	Vertical InAs-Si Gate-All-Around Tunnel FETs Integrated on Si Using Selective Epitaxy in Nanotube Templates. <i>IEEE Journal of the Electron Devices Society</i> , 2015, 3, 176-183.	1.2	104
6	InAs Quantum Dot Arrays Decorating the Facets of GaAs Nanowires. <i>ACS Nano</i> , 2010, 4, 5985-5993.	7.3	99
7	Thermal conductivity of GaAs nanowires studied by micro-Raman spectroscopy combined with laser heating. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	96
8	Suppression of three dimensional twinning for a 100% yield of vertical GaAs nanowires on silicon. <i>Nanoscale</i> , 2012, 4, 1486.	2.8	73
9	Mobility and carrier density in p-type GaAs nanowires measured by transmission Raman spectroscopy. <i>Nanoscale</i> , 2012, 4, 1789.	2.8	60
10	In(Ga)As quantum dot formation on group-III assisted catalyst-free InGaAs nanowires. <i>Nanotechnology</i> , 2011, 22, 195601.	1.3	48
11	Compensation mechanism in silicon-doped gallium arsenide nanowires. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	43
12	Pressure Tuning of the Optical Properties of GaAs Nanowires. <i>ACS Nano</i> , 2012, 6, 3284-3291.	7.3	43
13	Long-range ordered self-assembled InAs quantum dots epitaxially grown on (110) GaAs. <i>Applied Physics Letters</i> , 2004, 85, 4750-4752.	1.5	35
14	Three-Dimensional Magneto-Photoluminescence as a Probe of the Electronic Properties of Crystal-Phase Quantum Disks in GaAs Nanowires. <i>Nano Letters</i> , 2013, 13, 5303-5310.	4.5	28
15	Controlled synthesis of InAs wires, dot and twin-dot array configurations by cleaved edge overgrowth. <i>Nanotechnology</i> , 2008, 19, 045303.	1.3	15
16	Supercooling of nanoscale Ga drops with controlled impurity levels. <i>Physical Review B</i> , 2011, 84, .	1.1	13
17	Tuning the response of non-allowed Raman modes in GaAs nanowires. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 095103.	1.3	7
18	Optical Properties of InAs Quantum Dot Array Ensembles with Predetermined Lateral Sizes from 20 to 40 nm. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 045201.	0.8	4

#	ARTICLE	IF	CITATIONS
19	Investigation of a contacting scheme for self-assembled cleaved edge overgrown InAs nanowires and quantum dot arrays. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 1620-1625.	0.8	0